

## SMALL SIGNAL PNP TRANSISTOR

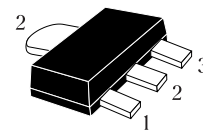
PRELIMINARY DATA

Type	Marking
BF621	621

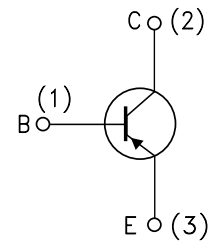
- SILICON EPITAXIAL PLANAR PNP HIGH VOLTAGE TRANSISTOR
- MINIATURE SOT-89 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BF620

### APPLICATIONS

- VIDEO AMPLIFIER CIRCUITS (RGB CATHODE CURRENT CONTROL)
- TELEPHONE WIRELINE INTERFACE (HOOK SWITCHES, DIALER CIRCUITS)


**SOT-89**

### INTERNAL SCHEMATIC DIAGRAM



SC08810

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	-300	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	-300	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	-5	V
$I_C$	Collector Current	-100	mA
$I_{CM}$	Collector Peak Current	-200	mA
$P_{tot}$	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	1.2	W
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

## BF621

### THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	104.1	$^{\circ}\text{C}/\text{W}$
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• Device mounted on a PCB area of  $1\text{ cm}^2$

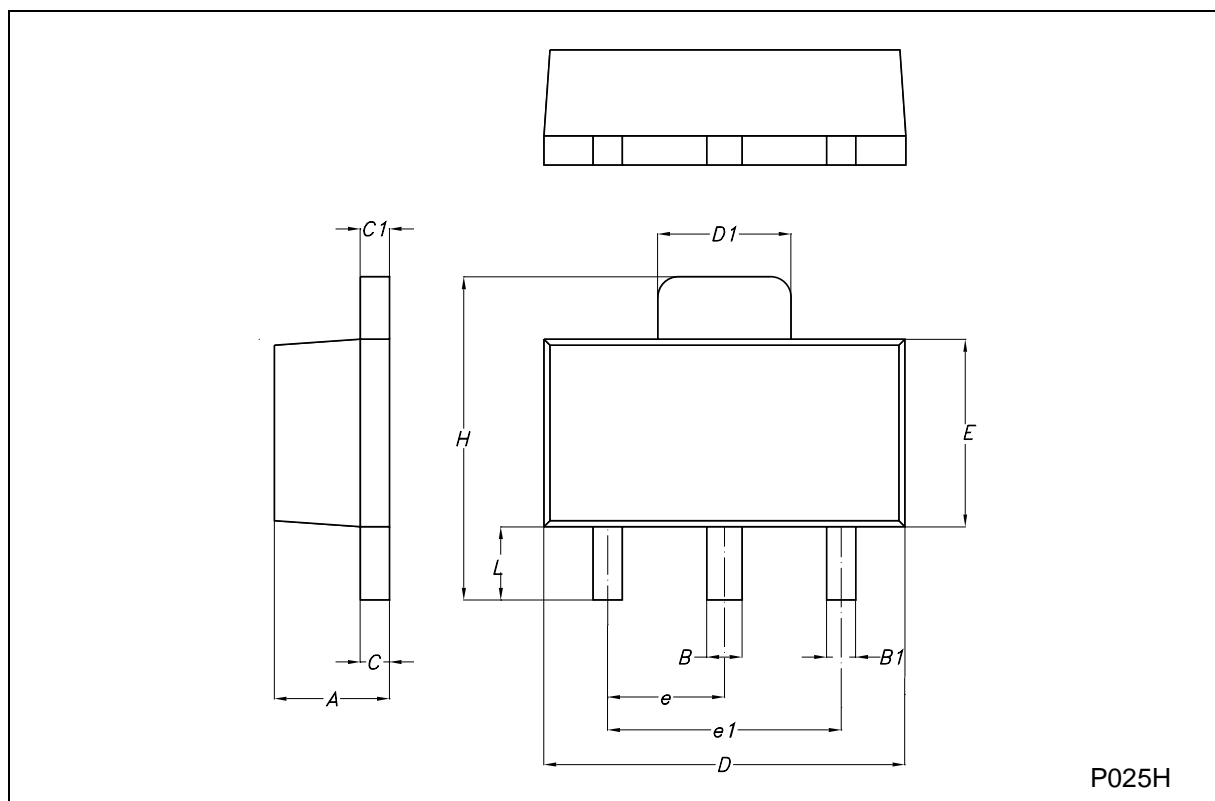
### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = -200\text{ V}$ $V_{CB} = -200\text{ V}$ $T_C = 150\text{ }^{\circ}\text{C}$ $V_{CB} = -300\text{ V}$			-10 -10 -100	nA $\mu\text{A}$ $\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = -5\text{ V}$			-50	nA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = -10\text{ mA}$	-300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_C = 0$ )	$I_E = -100\text{ }\mu\text{A}$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -30\text{ mA}$ $I_B = -5\text{ mA}$			-0.6	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = -30\text{ mA}$ $I_B = -5\text{ mA}$			-1.2	V
$h_{FE}^*$	DC Current Gain	$I_C = -25\text{ mA}$ $V_{CE} = -20\text{ V}$	50			
$f_T$	Transition Frequency	$I_C = -15\text{ mA}$ $V_{CE} = -10\text{ V}$ $f = 100\text{ MHz}$	60			MHz
$C_{RE}$	Reverse Capacitance	$I_E = 0$ $V_{CB} = -30\text{ V}$ $f = 1\text{ MHz}$			1.6	pF

\* Pulsed: Pulse duration =  $300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

## SOT-89 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.4		1.6	55.1		63.0
B	0.44		0.56	17.3		22.0
B1	0.36		0.48	14.2		18.9
C	0.35		0.44	13.8		17.3
C1	0.35		0.44	13.8		17.3
D	4.4		4.6	173.2		181.1
D1	1.62		1.83	63.8		72.0
E	2.29		2.6	90.2		102.4
e	1.42		1.57	55.9		61.8
e1	2.92		3.07	115.0		120.9
H	3.94		4.25	155.1		167.3
L	0.89		1.2	35.0		47.2



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